

### **Product Overview**

The APTGX50H120T1G device is a full bridge 1200V, 50A Insulated-Gate Bipolar Transistor (IGBT) 7 power module.

The following figures show the electrical diagram and pinout location of the device.

Figure 1. Electrical Diagram

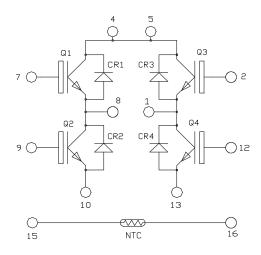
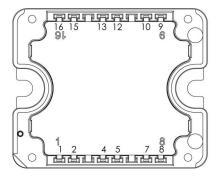


Figure 2. Pinout Location



#### **Notes:**

- Pins 4/5 must be shorted together.
- All ratings are at  $T_I = 25$  °C, unless otherwise specified.



These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

#### **Features**

The APTGX50H120T1G device has the following key features:

- IGBT 7
  - Low-voltage drop
  - Low-leakage current
- · Very low-stray inductance
- Internal thermistor for temperature monitoring
- Al<sub>2</sub>O<sub>3</sub> substrate and copper base plate

### **Benefits**

The APTGX50H120T1G device has the following benefits:

- · Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- · Low profile
- RoHS compliant

## **Potential Applications**

The APTGX50H120T1G device has the following potential applications:

- · Welding converters
- Switched-mode power supplies
- Uninterruptible power supplies
- Electric Vehicle (EV) motor and traction drive



## 1. Electrical Specifications

The following sections show the electrical specifications of the APTGX50H120T1G device.

### 1.1 IGBT Characteristics (Per IGBT)

The following table lists the absolute maximum ratings (per IGBT) of the APTGX50H120T1G device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Parameter		Unit
V <sub>CES</sub>	Collector-emitter voltage	ullector-emitter voltage		V
1	Continuous collector current	T <sub>C</sub> = 25 °C	90	
IC	Continuous collector current	T <sub>C</sub> = 120 °C 50		Α
I <sub>CM</sub>	Pulsed collector current, t <sub>P</sub> limite	Pulsed collector current, t <sub>P</sub> limited by T <sub>J(max)</sub>		
\/	Gate-emitter voltage		±20	
$V_{GE}$	Transient gate-emitter voltage	Transient gate-emitter voltage		V
P <sub>D</sub>	Power dissipation	T <sub>C</sub> = 25 °C	276	W

The following table lists the electrical characteristics (per IGBT) of the APTGX50H120T1G device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Zero gate voltage collector current	V <sub>GE</sub> = 0V; V <sub>CE</sub> = 1200V		_	_	10	μΑ
		\/ 45\/	T <sub>J</sub> = 25 °C	_	1.55	1.8	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	$V_{GE} = 15V$ $I_C = 50A$	T <sub>J</sub> = 125 °C	_	1.64	_	V
	Sacaración voltage	IC - 30A	T <sub>J</sub> = 175 °C	_	1.72	_	V
V <sub>GE(th)</sub>	Gate threshold voltage	$V_{GE} = V_{CE}$ ; $I_{C} = 1.3 \text{ mA}$	$V_{GE} = V_{CE}$ ; $I_{C} = 1.3 \text{ mA}$		5.8	6.45	
I <sub>GES</sub>	Gate-emitter leakage current	V <sub>GE</sub> = 20V; V <sub>CE</sub> = 0V		_	_	150	nA



The following table lists the dynamic characteristics (per IGBT) of the APTGX50H120T1G device.

 Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C <sub>ies</sub>	Input capacitance	V <sub>GE</sub> = 0V		_	11.1	<b>—</b>	
C <sub>oes</sub>	Output capacitance	$V_{CE} = 25V$		_	0.14	_	nF
C <sub>res</sub>	Reverse transfer capacitance	f = 100 kHz		_	0.04	_	- 111
$Q_{G}$	Gate charge	$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 50A$		_	0.92	_	μC
			T <sub>J</sub> = 25 °C	_	165	_	
T <sub>d(on)</sub>	Turn-on delay time	urn-on delay time	T <sub>J</sub> = 125 °C	_	167	_	
			T <sub>J</sub> = 175 °C	_	168	_	
			T <sub>J</sub> = 25 °C	_	41	_	
T <sub>r</sub>	Rise time	$V_{GE} = \pm 15V$	T <sub>J</sub> = 125 °C	_	45	_	
		V <sub>Bus</sub> = 600V	T <sub>J</sub> = 175 °C	_	47	_	
		I <sub>C</sub> = 50A	T <sub>J</sub> = 25 °C	_	260	_	ns
T <sub>d(off)</sub>	Turn-off delay time	me	T <sub>J</sub> = 125 °C	_	340	_	
			T <sub>J</sub> = 175 °C	_	380	_	
			T <sub>J</sub> = 25 °C	_	110	_	
T <sub>f</sub>	Fall time		T <sub>J</sub> = 125 °C	_	210	<u> </u>	
			T <sub>J</sub> = 175 °C	_	270	_	
		V <sub>GE</sub> = ±15V	T <sub>J</sub> = 25 °C	_	4.9	_	
E <sub>on</sub>	Turn-on energy	V <sub>Bus</sub> = 600V	T <sub>J</sub> = 125 °C	_	6.3	_	
		I <sub>C</sub> = 50A	T <sub>J</sub> = 175 °C	_	7.3	_	ml
		$R_G = 7.5\Omega$	T <sub>J</sub> = 25 °C	_	3.2	<u> </u>	mJ
E <sub>off</sub>	Turn-off energy	di/dt = 885A/µs	T <sub>J</sub> = 125 °C	_	5.2	_	
		dv/dt = 3000V/µs	T <sub>J</sub> = 175 °C	_	6.3	_	
R <sub>Gint</sub>	Internal gate resistar	ice		_	0	_	Ω
Chart size it date	$V_{GE} \le 15V$ $V_{Bus} = 800V$ $t_P \le 8 \mu s$	T <sub>J</sub> = 150 °C	_	190	_		
I <sub>sc</sub>	Short circuit data	$V_{GE} \le 15V$ $V_{Bus} = 800V$ $t_P \le 7 \mu s$	T <sub>J</sub> = 175 °C	_	180	_	A
R <sub>thJC</sub>	Junction-to-case ther	mal resistance		_	_	0.543	°C/W



## 1.2 Diode Characteristics (Per Diode)

The following table lists the diode characteristics (per diode) of the APTGX50H120T1G device.

Table 1-4. Diode Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
V <sub>RRM</sub>	Peak repetitive reverse volt	age	e		_	1200	٧
I <sub>RM</sub>	Reverse leakage current	V <sub>R</sub> = 1200V		_	_	5	μΑ
I <sub>FRM</sub>	Repetitive forward current,	t <sub>P</sub> limited by T <sub>J(max)</sub>		_	_	100	Α
l <sup>2</sup> t	l <sup>2</sup> t value	t <sub>p</sub> = 10 ms	T <sub>J</sub> = 125 °C	_	_	465	A 2-
I <del>-</del> [	1-t value	$V_R = 0V$	T <sub>J</sub> = 175 °C	_	_	420	A <sup>2</sup> S
l <sub>F</sub>	DC forward current	T <sub>C</sub> = 95 °C	T <sub>J</sub> = 175 °C	_	50		Α
	- Diode forward voltage	I <sub>F</sub> = 50A	T <sub>J</sub> = 25 °C	_	1.75	1.95	
V <sub>F</sub>		$V_{GE} = 0A$	T <sub>J</sub> = 125 °C	_	1.6	_	V
			T <sub>J</sub> = 175 °C	_	1.52	_	
			T <sub>J</sub> = 25 °C	_	25	_	
I <sub>RRM</sub>	Reverse recovery current		T <sub>J</sub> = 125 °C	_	33	_	Α
		V <sub>GE</sub> = -15V	T <sub>J</sub> = 175 °C	_	38	_	
		I <sub>F</sub> = 50A	$T_J = 25  ^{\circ}C$		3.2		
Q <sub>rr</sub>	Reverse recovery charge	$V_R = 600V$	T <sub>J</sub> = 125 °C		6.5		μC
		di/dt = 885 A/µs	T <sub>J</sub> = 175 °C		8.9		
		ļ ,	$T_J = 25 ^{\circ}C$	_	1		
E <sub>rr</sub>	Reverse recovery energy		T <sub>J</sub> = 125 °C	_	2.2	_	mJ
			T <sub>J</sub> = 175 °C	_	3.2	_	
$R_{thJC}$	Junction-to-case thermal re	sistance		_	_	0.87	°C/W



### 1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the APTGX50H120T1G device.

**Table 1-5.** Thermal and Package Characteristics

Symbol	Characteristic					Тур.	Max.	Unit
V <sub>ISOL</sub>	RMS isolation voltage, any terminal-to	-case t = 1	1 min, 50	/60 Hz	4000	_	_	V
d <sub>creep</sub>	Creepage distance terminal-to-heatsin	nk			_	13.4	_	mm
d <sub>clear</sub>	Clearance distance terminal-to-heatsi	nk			_	12.8	_	mm
R <sub>CE</sub>	Lead resistance terminal-to-chip		$T_{C} = 25^{\circ}$	C, per switch	_	3	_	mΩ
T <sub>J</sub>	Operating junction temperature range	e			-40	_	175	
T <sub>STG</sub>	Storage temperature range				-40	_	125	°C
T <sub>C</sub>	Operating case temperature				-40	_	125	
$\tau_{M}$	Mounting torque To heatsink M4				2	_	3	N.m
Wt	Package weight				_	66	_	g

The following table lists the temperature sensor NTC of the APTGX50H120T1G device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristic		Min.	Тур.	Max.	Unit
R <sub>25</sub>	Resistance at 25 °C		_	50	_	kΩ
$\Delta R_{25}/R_{25}$	_		_	5	_	%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15K		_	3952	_	K
ΔΒ/Β	_	T <sub>C</sub> = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

**Note:** For more information, see APT0406—Using NTC Temperature Sensor Integrated into Power Module.



### 1.4 Typical IGBT Performance Curve

The following figures show the IGBT performance curves of the APTGX50H120T1G device.

Figure 1-1. Maximum Thermal Impedance

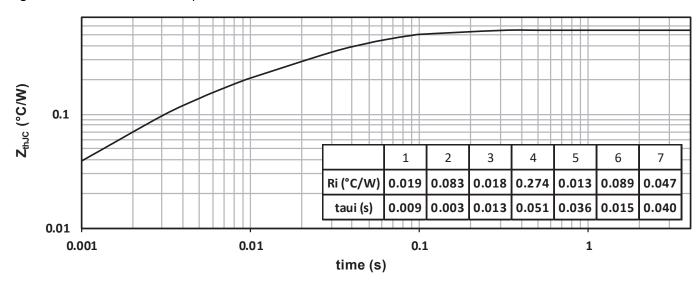


Figure 1-2. Output Characteristics, V<sub>GE</sub> = 15V

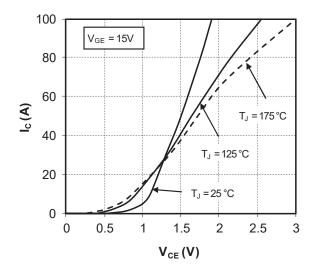


Figure 1-3. Output Characteristics,  $T_1 = 175 \, ^{\circ}\text{C}$ 

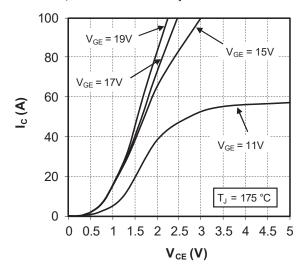


Figure 1-4. Switching Losses vs. Gate Resistance

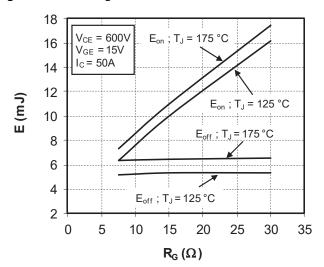


Figure 1-6. Operating Frequency vs. Collector Current

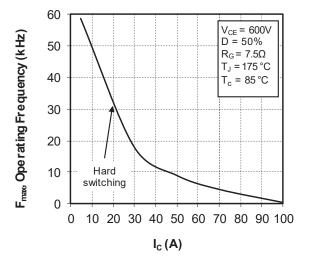


Figure 1-5. Switching Losses vs. Collector Current

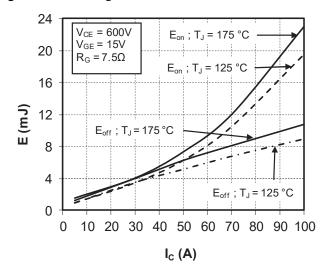


Figure 1-7. Gate Charge Characteristics

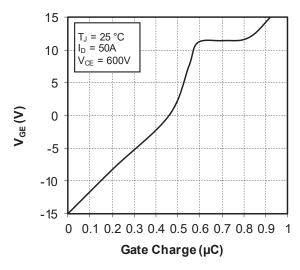


Figure 1-8. Transfer Characteristics

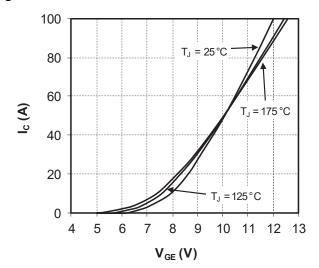


Figure 1-9. Capacity Characteristics

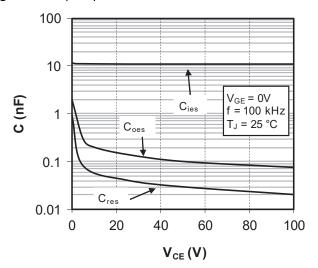
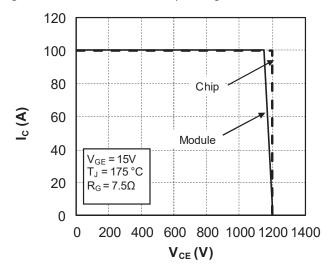


Figure 1-10. Reverse Bias Safe Operating Area





### 1.5 Typical Diode Performance Curve

The following figures show the diode performance curves of the APTGX50H120T1G device.

Figure 1-11. Maximum Thermal Impedance

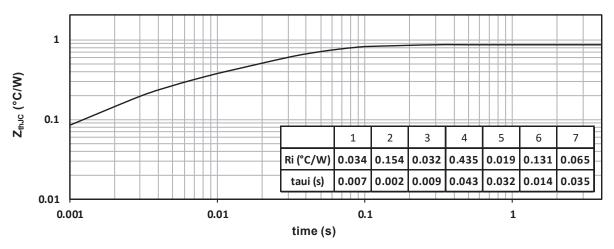


Figure 1-12. Forward Characteristics

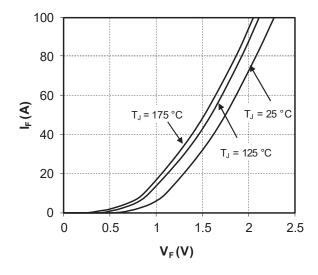


Figure 1-13. Switching Losses vs. Gate Resistance

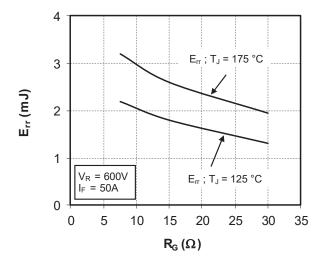
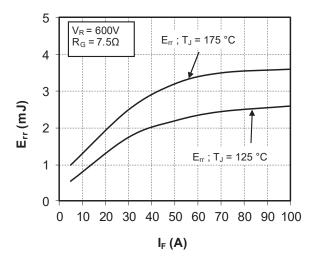


Figure 1-14. Switching Losses vs. Forward Current





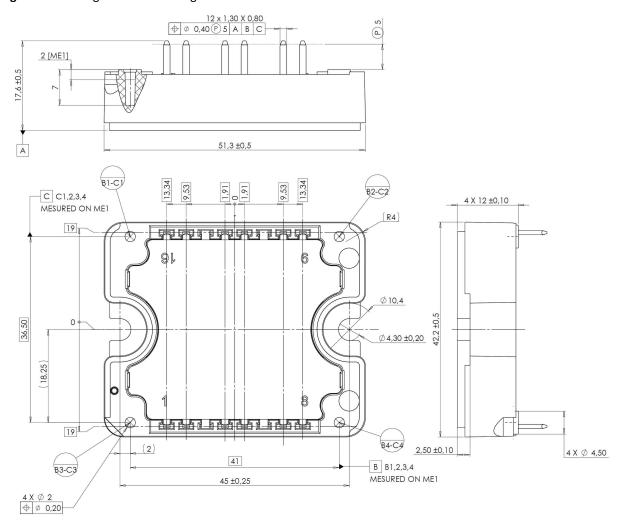
## 2. Package Specifications

The following section shows the package specification of the APTGX50H120T1G device.

### 2.1 Package Outline

The following figure shows the package outline drawing of the APTGX50H120T1G device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



**Note:** For more information, see application note AN3500A - Mounting instructions for SP1F and SP3F power modules.



## 3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Revision	Date	Description
Α	09/2024	Initial revision



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ISBN: 978-1-6683-0219-4

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